

## Description

The SX5P04MI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = -40V$   $I_D = -5.0A$

$R_{DS(ON)} < 72m\Omega$  @  $V_{GS} = -10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



## Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Steady State	Units
V <sub>DS</sub>	Drain-Source Voltage	-40	V
V <sub>GS</sub>	Gate-Source Voltage	$\pm 20$	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-5.0	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-3.0	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-16.1	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1.32	W
P <sub>D</sub> @T <sub>A</sub> =70°C	Total Power Dissipation <sup>3</sup>	0.84	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	125	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	80	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=-250\mu\text{A}$	-40	-46	---	V
$\Delta BVDSS/\Delta TJ$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	---	-0.018	---	$\text{V}/^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-4.5\text{V}$ , $I_D=-3\text{A}$	---	65	72	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$ , $I_D=-2\text{A}$	---	89	100	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250\mu\text{A}$	-1.0	-1.5	-2.5	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	2.5	---	$\text{mV}/^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=-24\text{V}$ , $V_{GS}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$V_{DS}=-24\text{V}$ , $V_{GS}=0\text{V}$ , $T_J=55^\circ\text{C}$	---	---	-5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$ , $V_{DS}=0\text{V}$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=-5\text{V}$ , $I_D=-3\text{A}$	---	5.8	---	S
Qg	Total Gate Charge (-4.5V)	$V_{DS}=-32\text{V}$ , $V_{GS}=-4.5\text{V}$ , $I_D=-3\text{A}$	---	6.4	---	nC
Qgs	Gate-Source Charge		---	2.1	---	
Qgd	Gate-Drain Charge		---	2.5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=-20\text{V}$ , $V_{GS}=-4.5\text{V}$ , $R_G=3.3\Omega$ , $I_D=-3\text{A}$	---	4.2	---	ns
Tr	Rise Time		---	23	---	
Td(off)	Turn-Off Delay Time		---	26.8	---	
Tf	Fall Time		---	20.6	---	
Ciss	Input Capacitance	$V_{DS}=-15\text{V}$ , $V_{GS}=0\text{V}$ , $f=1\text{MHz}$	---	620	---	pF
Coss	Output Capacitance		---	65	---	
Crss	Reverse Transfer Capacitance		---	53	---	
IS	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0\text{V}$ , Force Current	---	---	-5.2	A
ISM	Pulsed Source Current <sup>2,4</sup>		---	---	-16.1	A
VSD	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0\text{V}$ , $I_S=-1\text{A}$ , $T_J=25^\circ\text{C}$	---	---	-1	V

**Note :**

- 1、The data tested by surface mounted on a 1 inch FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3、The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4、The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

## Typical Characteristics

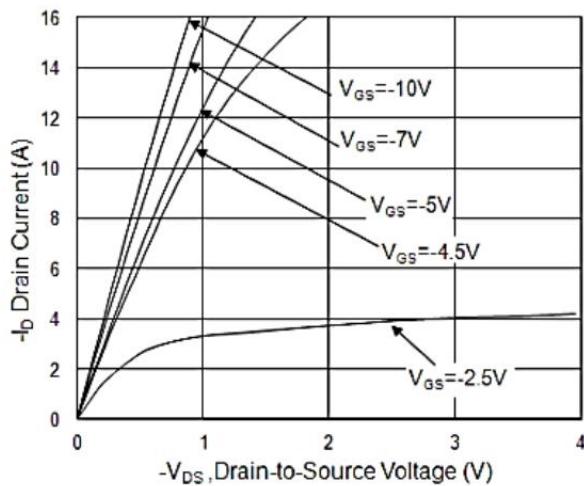


Fig.1 Typical Output Characteristics

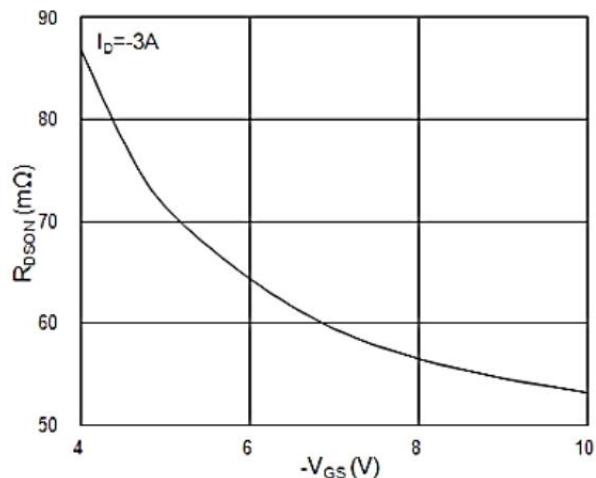


Fig.2 On-Resistance vs. G-S Voltage

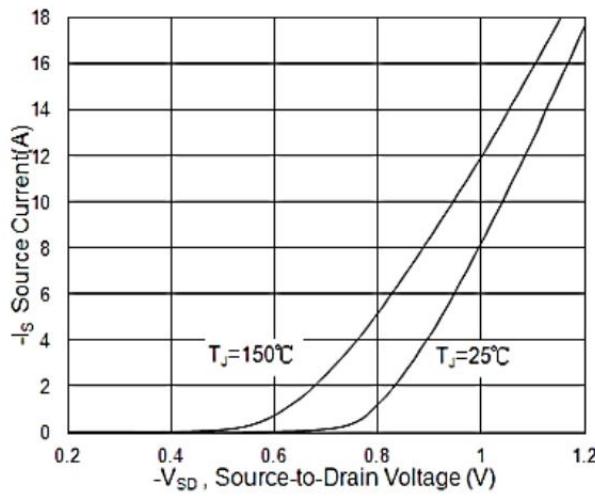


Fig.3 Forward Characteristics Of Reverse

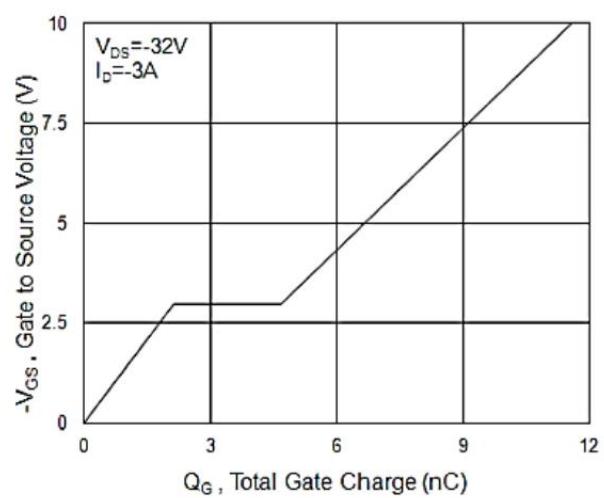


Fig.4 Gate-Charge Characteristics

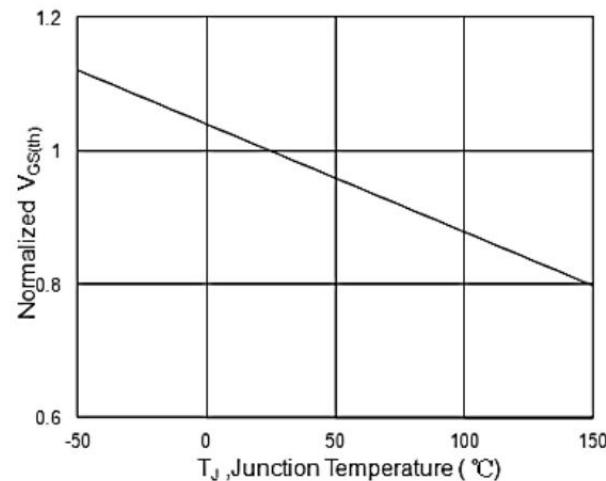


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

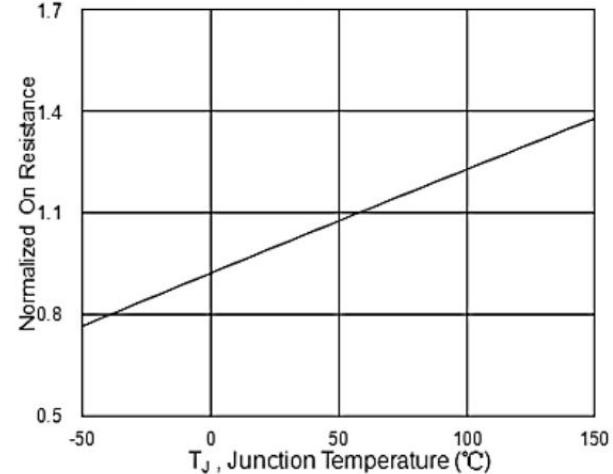


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

## Typical Characteristics

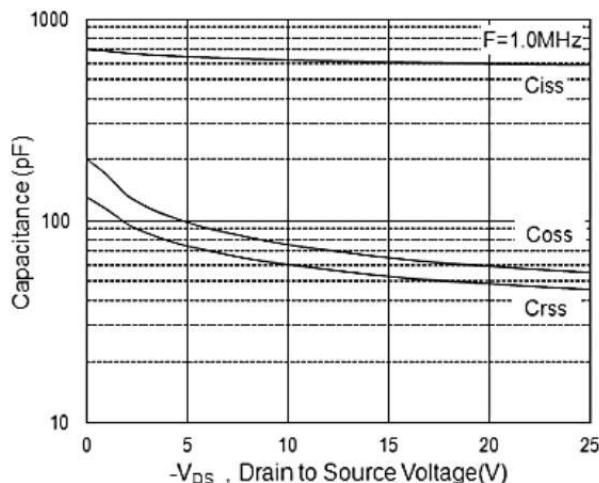


Fig.7 Capacitance

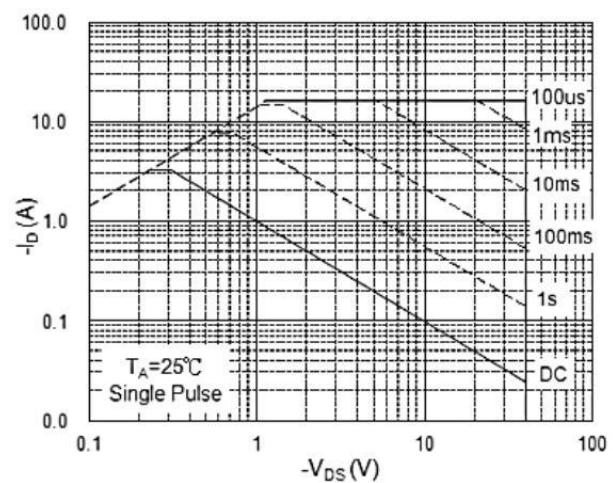


Fig.8 Safe Operating Area

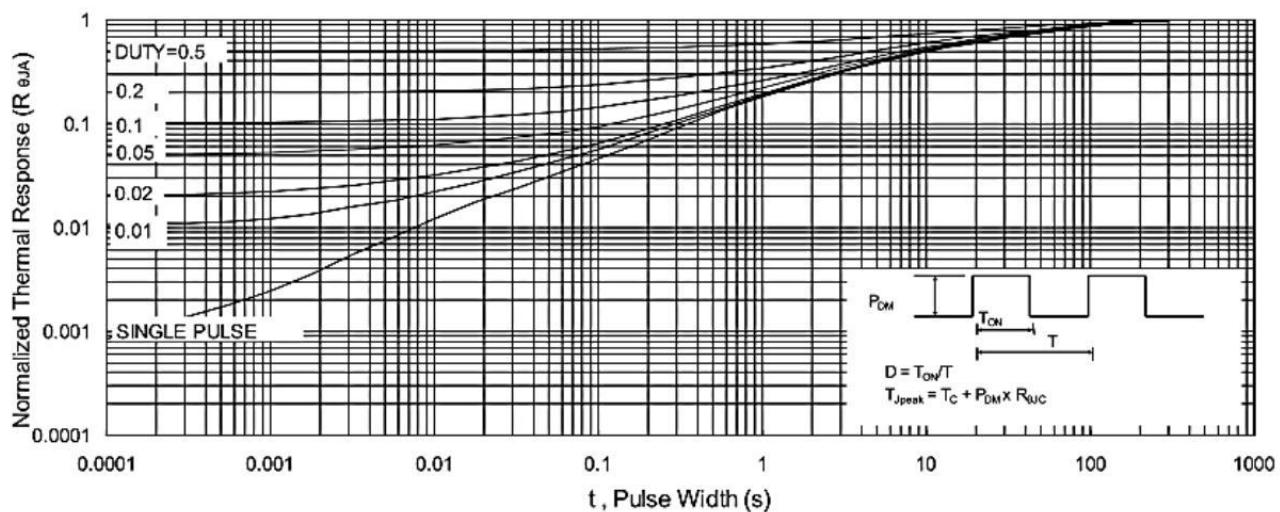


Fig.9 Normalized Maximum Transient Thermal Impedance

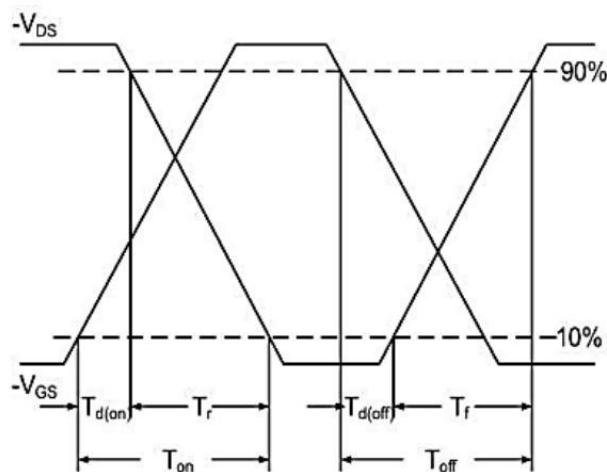


Fig.10 Switching Time Waveform

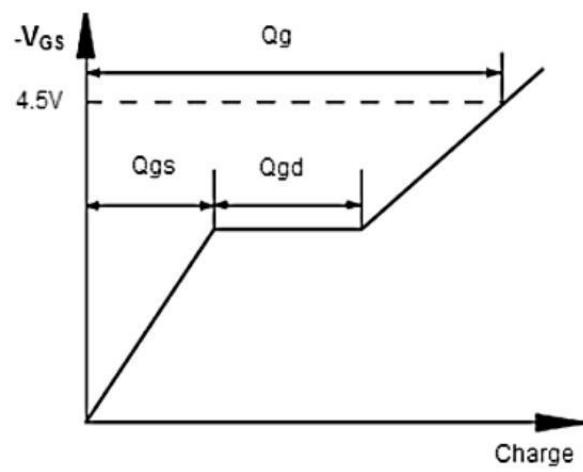
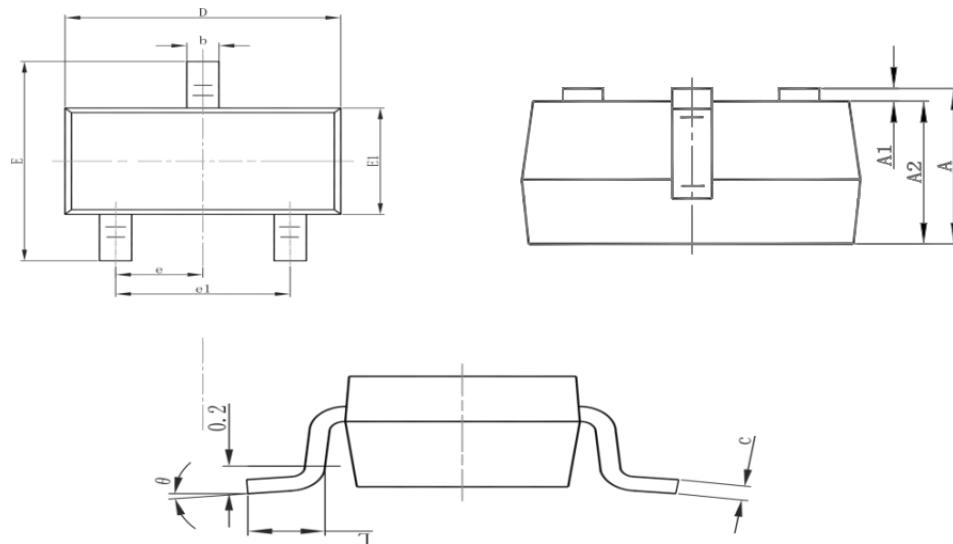


Fig.11 Gate Charge Waveform

## Package Mechanical Data:SOT23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23-3L		3000